

ABSTRACT OF THE DISCLOSURE

In a semiconductor device, a wiring pattern groove is formed in a surface portion of a silicon oxide film provided above a semiconductor substrate.

5 A wiring layer is buried into the wiring pattern groove
with a barrier metal film interposed therebetween.
The barrier metal film is selectively removed from
each sidewall portion of the wiring pattern groove.
In other words, the barrier metal film is left only
10 on the bottom of the wiring pattern groove. Thus,
a damascene wiring layer having a hollow section whose
dielectric constant is low between each sidewall of
the wiring pattern groove and each side of the wiring
layer can be formed in the semiconductor device.